

1. Description

SS055N08DS, the N-channel Enhanced Power MOSFETs, is obtained by advanced double trench technology which reduce the conduction loss, improve switching performance and enhance the avalanche energy. This is suitable device for DC-DC and high speed switching applications.

KEY CHARACTERISTICS

Parameter	Value	Unit
V_{DS}	85	V
I_D	100	A
$R_{DS(on).typ}$	4.5	mΩ

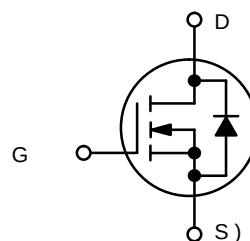
FEATURES

- Fast Switching
- Low On-Resistance ($R_{DS(on)} \leq 5.5m\Omega$)
- Low Gate Charge
- Low Reverse transfer capacitances
- High avalanche ruggedness
- RoHS product

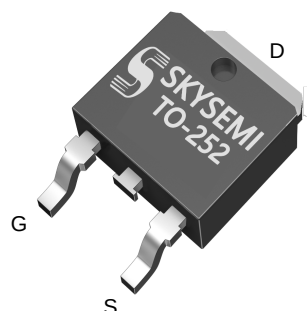
APPLICATIONS

- Switching applications
- DC-DC Converters
- BMS

Schematic Diagram



TO-252



ORDERING INFORMATION

Ordering Code	Package	Product Code	Packing	Quantity
SS055N08DS	TO-252	SS055N08DS	Reel	2500